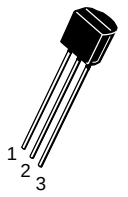
General Purpose Transistors
NPN Silicon

2N4401

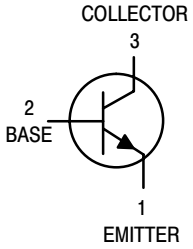
ON Semiconductor Preferred Device

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V_{CEO}	40	Vdc
Collector–Base Voltage	V_{CBO}	60	Vdc
Emitter–Base Voltage	V_{EBO}	6.0	Vdc
Collector Current — Continuous	I_C	600	mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	625 5.0	mW mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	1.5 12	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	–55 to +150	°C



CASE 29–11, STYLE 1
TO–92 (TO–226AA)



THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector–Emitter Breakdown Voltage(1) (I_C = 1.0 mAdc, I_B = 0)	$V_{(BR)CEO}$	40	—	Vdc
Collector–Base Breakdown Voltage (I_C = 0.1 mAdc, I_E = 0)	$V_{(BR)CBO}$	60	—	Vdc
Emitter–Base Breakdown Voltage (I_E = 0.1 mAdc, I_C = 0)	$V_{(BR)EBO}$	6.0	—	Vdc
Base Cutoff Current (V_{CE} = 35 Vdc, V_{EB} = 0.4 Vdc)	I_{BEV}	—	0.1	μAdc
Collector Cutoff Current (V_{CE} = 35 Vdc, V_{EB} = 0.4 Vdc)	I_{CEX}	—	0.1	μAdc

1. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

Preferred devices are ON Semiconductor recommended choices for future use and best overall value.

June, 2001 – Rev. 0
Publication Order Number:
2N4401/D

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted) (Continued)

Characteristic	Symbol	Min	Max	Unit
ON CHARACTERISTICS(1)				
DC Current Gain	h_{FE}			—
(I_C = 0.1 mAdc, V_{CE} = 1.0 Vdc)		20	—	
(I_C = 1.0 mAdc, V_{CE} = 1.0 Vdc)		40	—	
(I_C = 10 mAdc, V_{CE} = 1.0 Vdc)		80	—	
(I_C = 150 mAdc, V_{CE} = 1.0 Vdc)		100	300	
(I_C = 500 mAdc, V_{CE} = 2.0 Vdc)		40	—	
Collector–Emitter Saturation Voltage (I_C = 150 mAdc, I_B = 15 mAdc)	$V_{CE(sat)}$	—	0.4	Vdc
(I_C = 500 mAdc, I_B = 50 mAdc)		—	0.75	
Base–Emitter Saturation Voltage (I_C = 150 mAdc, I_B = 15 mAdc)	$V_{BE(sat)}$	0.75	0.95	Vdc
(I_C = 500 mAdc, I_B = 50 mAdc)		—	1.2	
SMALL–SIGNAL CHARACTERISTICS				
Current–Gain — Bandwidth Product	f_T			MHz
(I_C = 20 mAdc, V_{CE} = 10 Vdc, f = 100 MHz)		250	—	
Collector–Base Capacitance (V_{CB} = 5.0 Vdc, I_E = 0, f = 1.0 MHz)	C_{cb}	—	6.5	pF
Emitter–Base Capacitance (V_{EB} = 0.5 Vdc, I_C = 0, f = 1.0 MHz)	C_{eb}	—	30	pF
Input Impedance	h_{ie}			k ohms
(I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)		1.0	15	
Voltage Feedback Ratio (I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	h_{re}	0.1	8.0	X 10^{-4}
Small–Signal Current Gain	h_{fe}			—
(I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)		40	500	
Output Admittance (I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	h_{oe}	1.0	30	μmhos
SWITCHING CHARACTERISTICS				
Delay Time	(V_{CC} = 30 Vdc, V_{BE} = 2.0 Vdc, I_C = 150 mAdc, I_{B1} = 15 mAdc)	t_d	—	15	ns
Rise Time		t_r	—	20	ns
Storage Time	(V_{CC} = 30 Vdc, I_C = 150 mAdc, I_{B1} = I_{B2} = 15 mAdc)	t_s	—	225	ns
Fall Time		t_f	—	30	ns

1. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

SWITCHING TIME EQUIVALENT TEST CIRCUITS

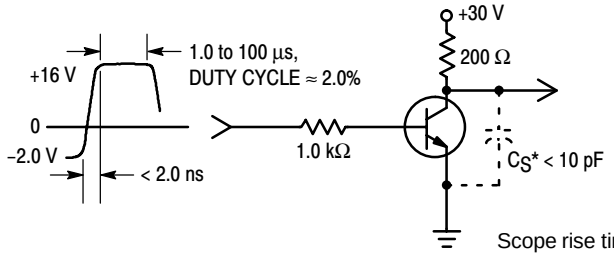


Figure 1. Turn–On Time

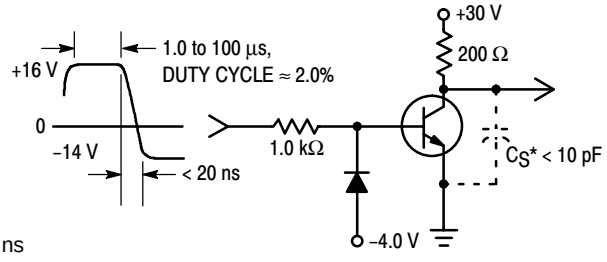


Figure 2. Turn–Off Time

Scope rise time < 4.0 ns
*Total shunt capacitance of test jig connectors, and oscilloscope

TRANSIENT CHARACTERISTICS

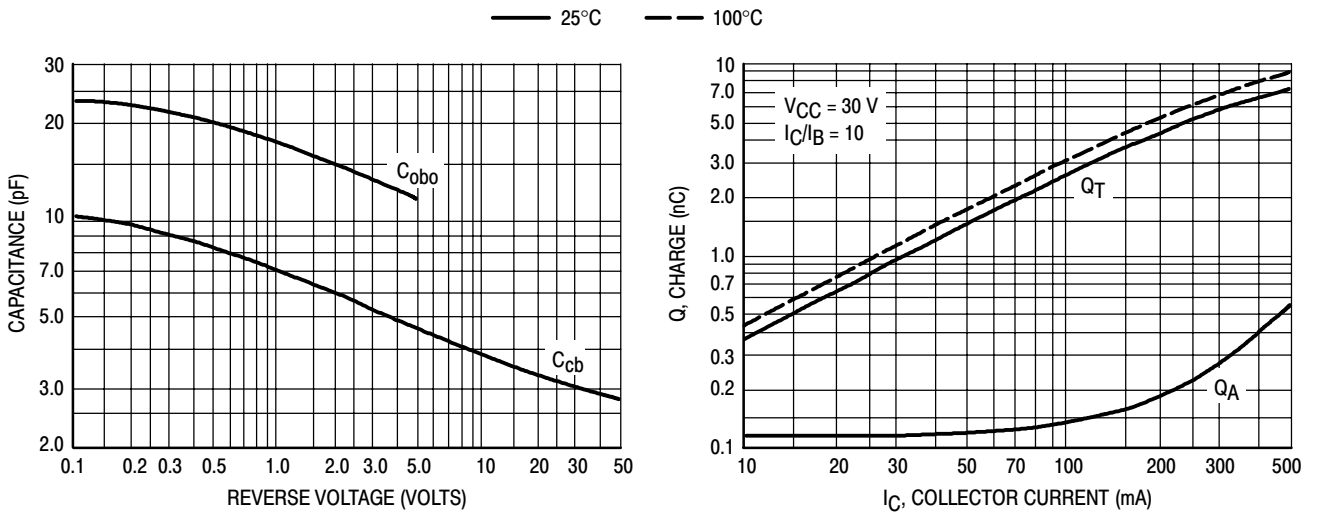


Figure 3. Capacitances

Figure 4. Charge Data

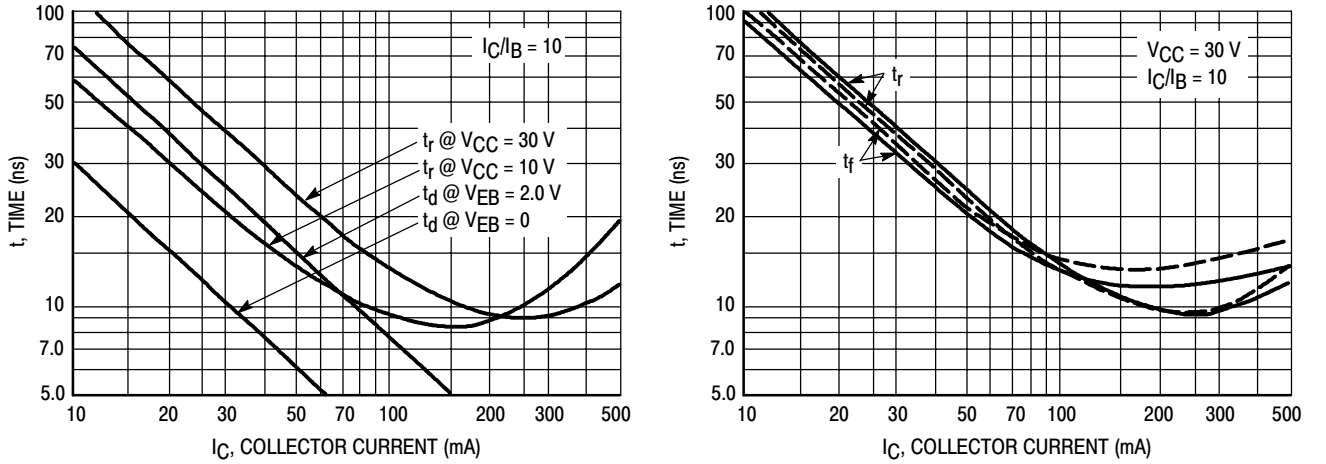


Figure 5. Turn–On Time

Figure 6. Rise and Fall Times

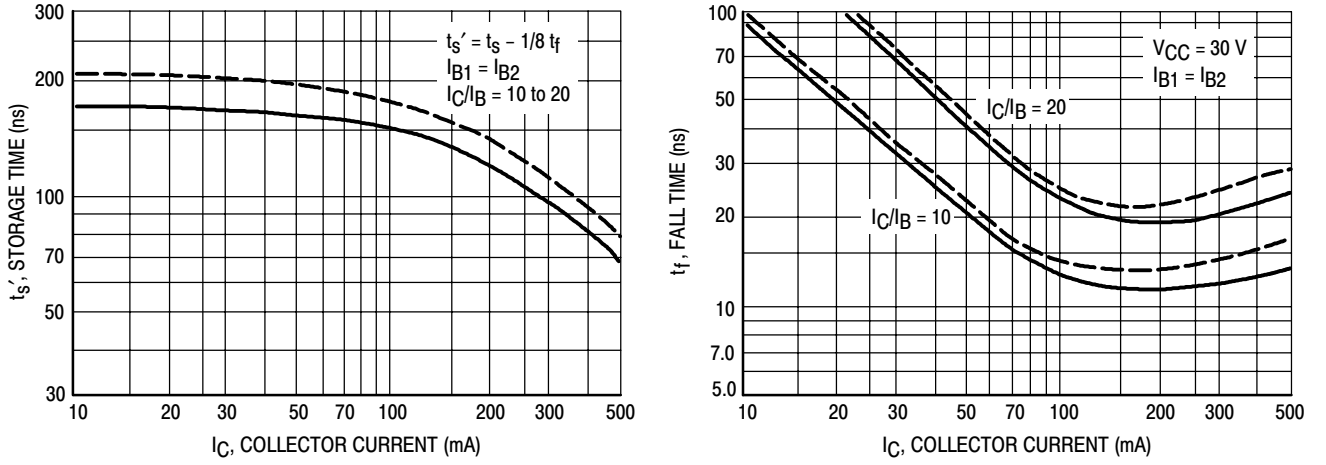


Figure 7. Storage Time

Figure 8. Fall Time

SMALL–SIGNAL CHARACTERISTICS

NOISE FIGURE

V_{CE} = 10 Vdc, T_A = 25°C; Bandwidth = 1.0 Hz

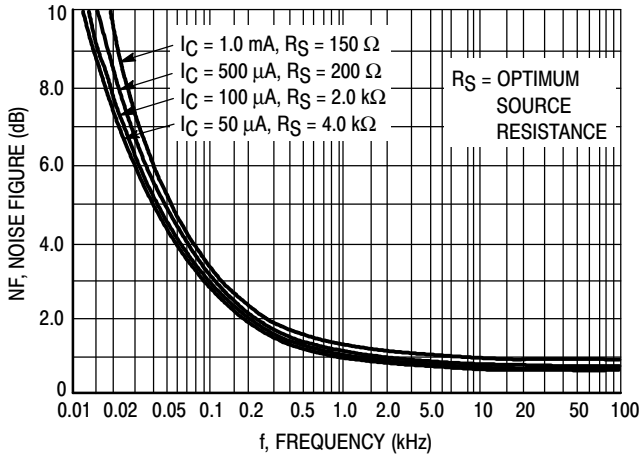


Figure 9. Frequency Effects

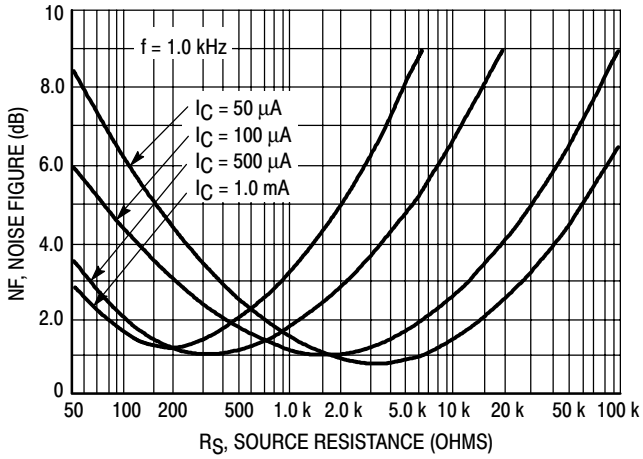


Figure 10. Source Resistance Effects

h PARAMETERS

V_{CE} = 10 Vdc, f = 1.0 kHz, T_A = 25°C

This group of graphs illustrates the relationship between h_{fe} and other "h" parameters for this series of transistors. To obtain these curves, a high–gain and a low–gain unit were selected from the 2N4401 lines, and the same units were used to develop the correspondingly numbered curves on each graph.

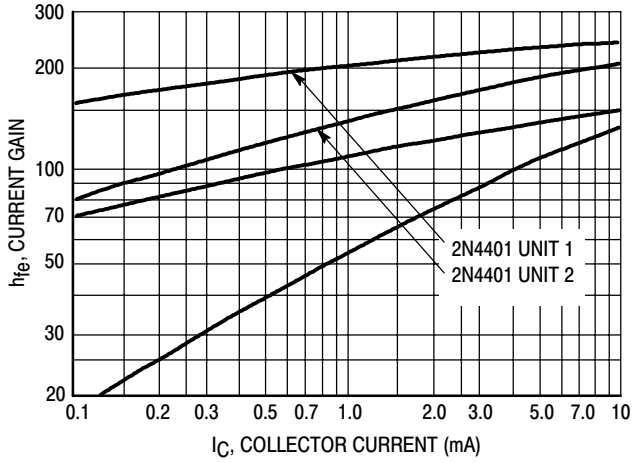


Figure 11. Current Gain

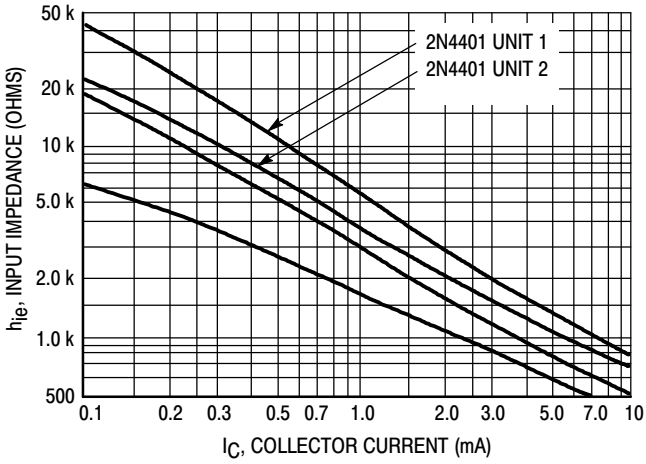


Figure 12. Input Impedance

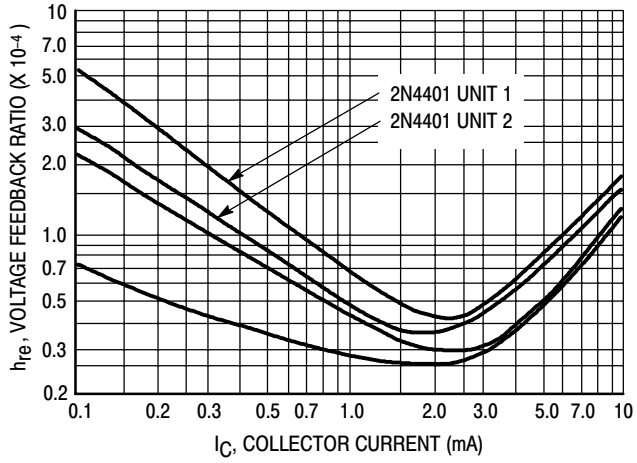


Figure 13. Voltage Feedback Ratio

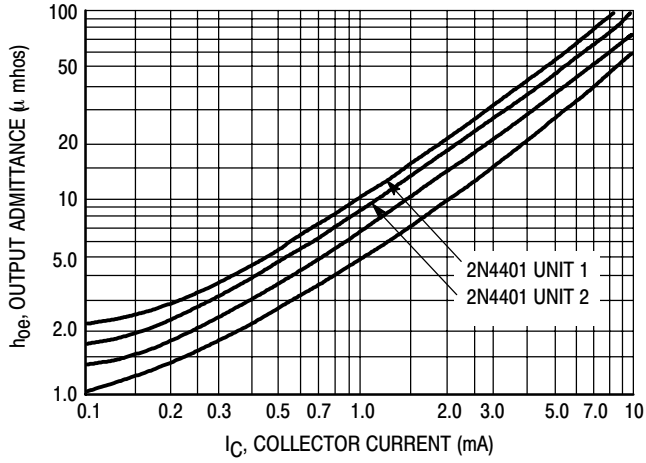


Figure 14. Output Admittance

STATIC CHARACTERISTICS

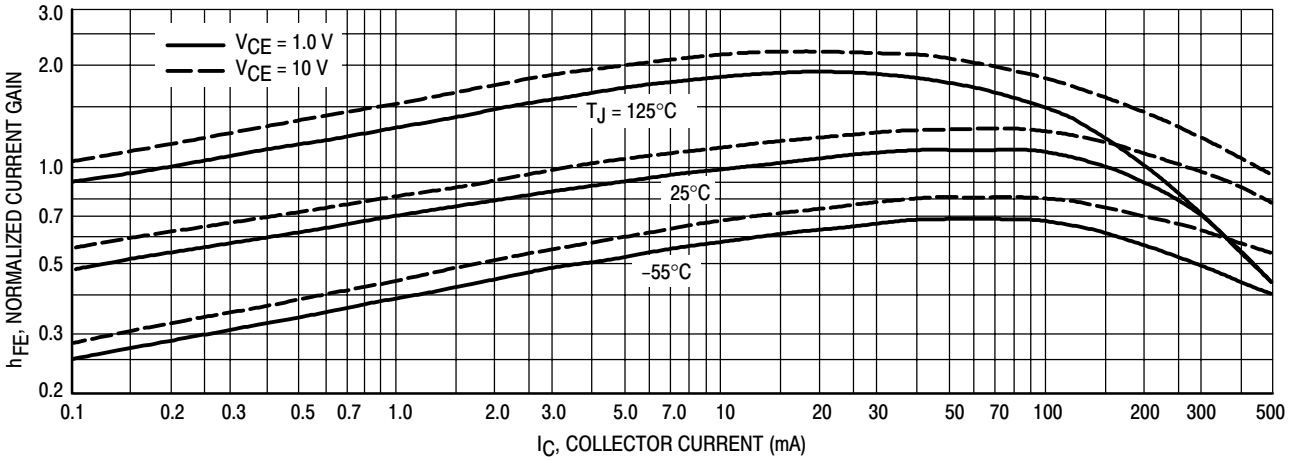


Figure 15. DC Current Gain

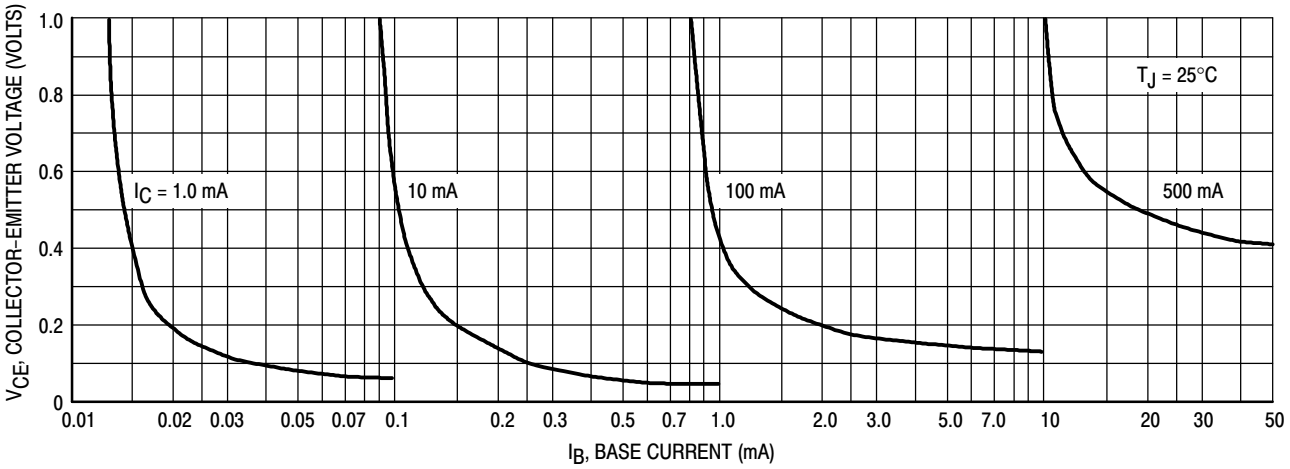


Figure 16. Collector Saturation Region

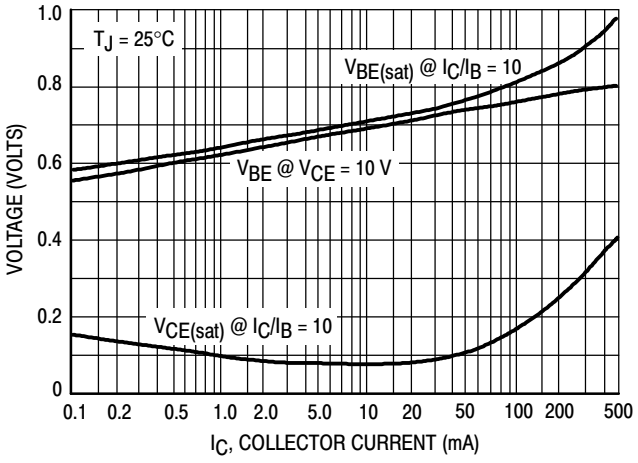


Figure 17. “On” Voltages

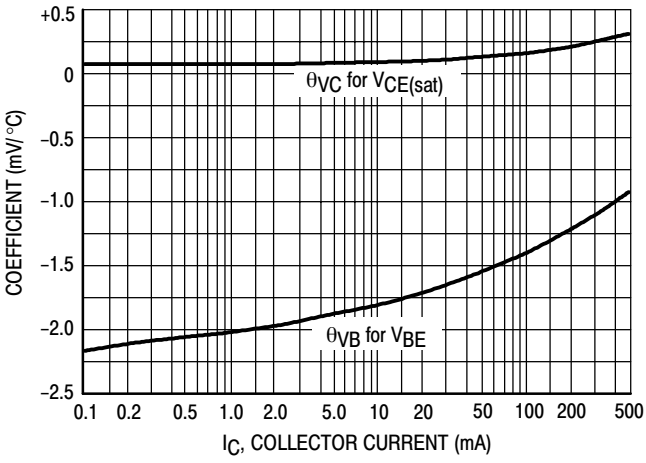
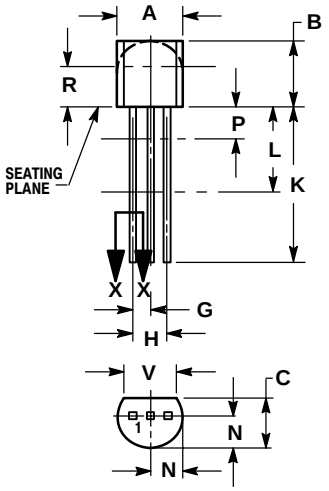
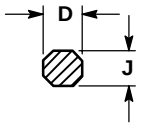


Figure 18. Temperature Coefficients

PACKAGE DIMENSIONS

TO–92 (TO–226)
CASE 29–11
ISSUE AL





SECTION X–X

STYLE 1:
PIN 1. EMITTER
2. BASE
3. COLLECTOR

NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.175	0.205	4.45	5.20
B	0.170	0.210	4.32	5.33
C	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
H	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500	---	12.70	---
L	0.250	---	6.35	---
N	0.080	0.105	2.04	2.66
P	---	0.100	---	2.54
R	0.115	---	2.93	---
V	0.135	---	3.43	---

Notes

PUBLICATION ORDERING INFORMATION

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